

Standard Rectifier

$$V_{RRM} = 1600 \text{ V}$$

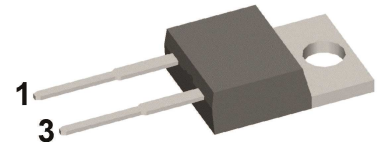
$$I_{FAV} = 10 \text{ A}$$

$$V_F = 1.21 \text{ V}$$

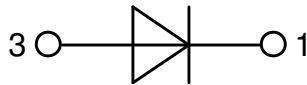
Single Diode

Part number

DMA10I1600PA



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

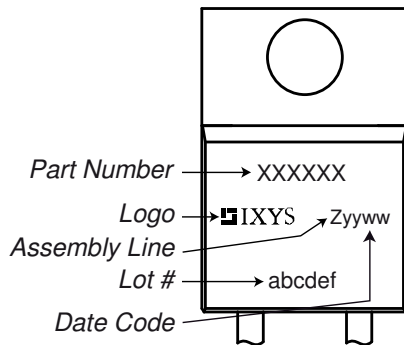
- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1700	V
V_{RRM}	max. repetitive reverse blocking voltage					1600	V
I_R	reverse current	$V_R = 1600$ V		$T_{VJ} = 25^\circ\text{C}$		10	μA
		$V_R = 1600$ V		$T_{VJ} = 150^\circ\text{C}$		0.2	mA
V_F	forward voltage drop	$I_F = 10$ A		$T_{VJ} = 25^\circ\text{C}$		1.26	V
		$I_F = 20$ A				1.53	V
		$I_F = 10$ A		$T_{VJ} = 150^\circ\text{C}$		1.21	V
		$I_F = 20$ A				1.57	V
I_{FAV}	average forward current	$T_C = 150^\circ\text{C}$	rectangular	$T_{VJ} = 175^\circ\text{C}$		10	A
V_{FO}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^\circ\text{C}$		0.82	V
r_F	slope resistance					37	m Ω
R_{thJC}	thermal resistance junction to case					1.5	K/W
R_{thCH}	thermal resistance case to heatsink				0.50		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		100	W
I_{FSM}	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		120	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		130	A
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		100	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		110	A
I^2t	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		72	A ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		70	A ² s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		50	A ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		50	A ² s
C_J	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		4	pF

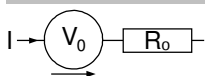
Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			25	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking

Part description

D = Diode
 M = Standard Rectifier
 A = (up to 1800V)
 10 = Current Rating [A]
 I = Single Diode
 1600 = Reverse Voltage [V]
 PA = TO-220AC (2)

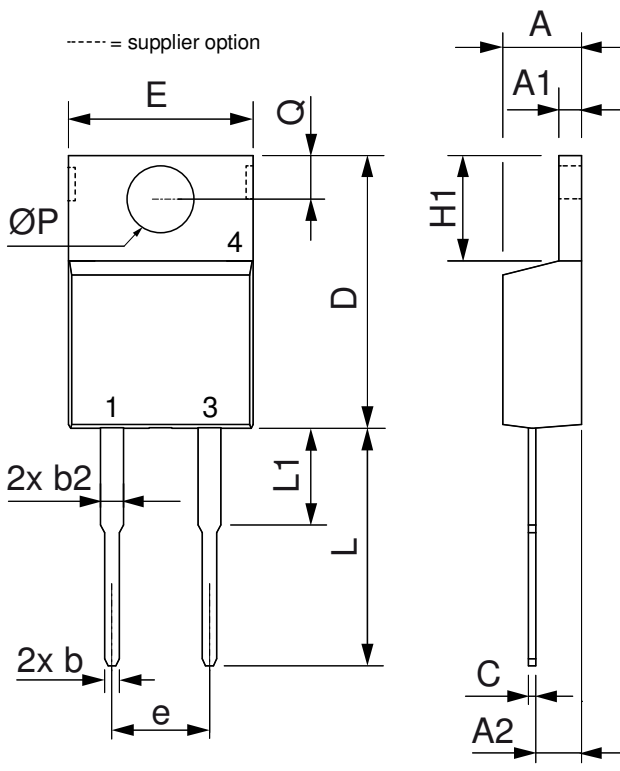
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DMA10I1600PA	DMA10I1600PA	Tube	50	508780

Similar Part	Package	Voltage class
DMA10IM1600PZ	TO-263AB (D2Pak) (2HV)	1600

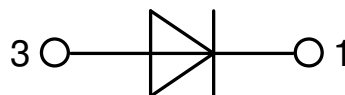
Equivalent Circuits for Simulation
** on die level*
 $T_{VJ} = 175\text{ °C}$

Rectifier

$V_{0\ max}$	threshold voltage	0.82	V
$R_{0\ max}$	slope resistance *	34	mΩ

Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



Rectifier

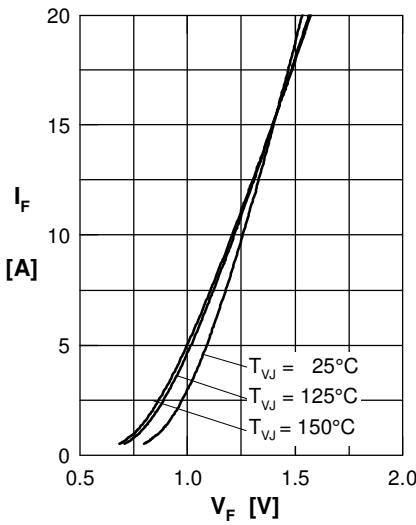


Fig. 1 Forward current versus voltage drop per diode

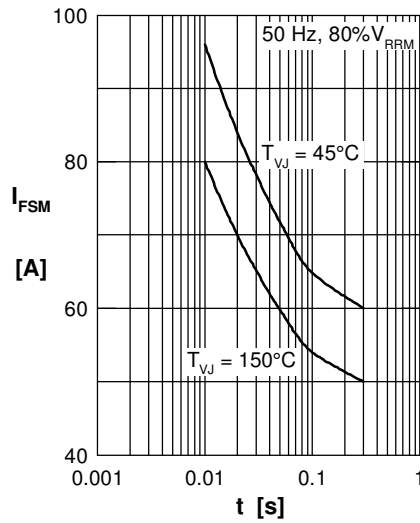


Fig. 2 Surge overload current

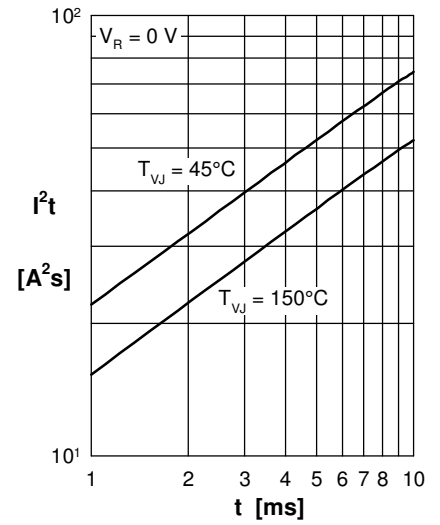


Fig. 3 I^2t versus time per diode

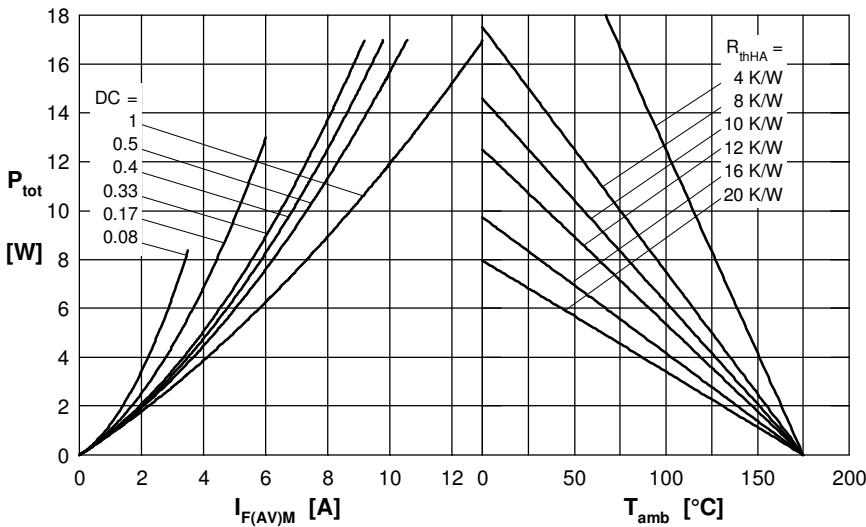


Fig. 4 Power dissipation vs. direct output current and ambient temperature

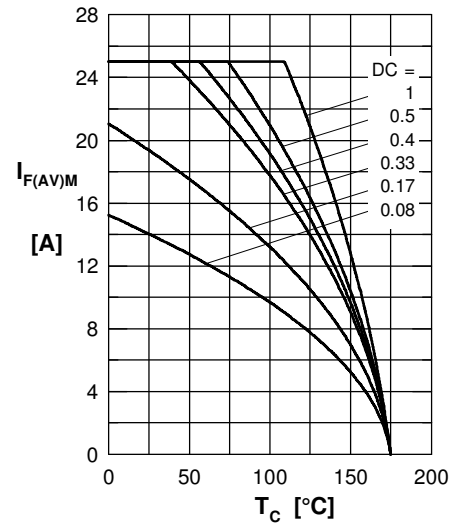


Fig. 5 Max. forward current vs. case temperature

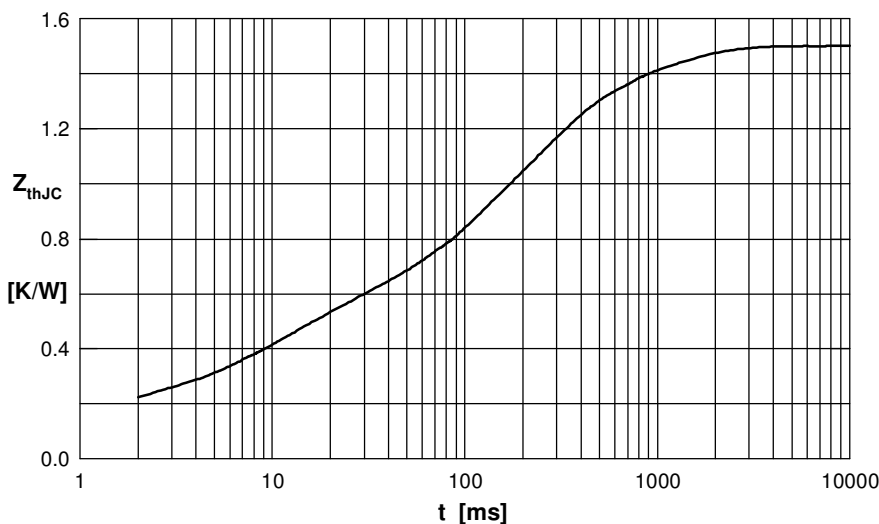


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.155	0.0005
2	0.332	0.0095
3	0.713	0.17
4	0.3	0.8